

Publications:

- 1) **Invited Review Article:** "Metal-Organic Vapor Phase Epitaxy of Compound Semiconductors", T.F. Kuech, Materials Science Reports 2 (1987) 1.
- 2) **Book Chapter:** "The Direct Optical Determination of the GaAs/Al_xGa_{1-x}As Valence Band Offsets", D.J. Wolford, T.F. Kuech, and M.Jaros, in_Heterojunction Band Discontinuities, Physics and Applications, Ed.F.Capasso and G.Margaritondo (North-Holland, Amsterdam (1987) 263.
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- 6) "Stability and Pinning Points in Substrate confined Liquids", J.O.McCaldin and T.F. Kuech, J. Appl. Phys. 52 (1981) 503.
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